

The Crystallines and Transport Properties of Manganite Thin Films with High Temperature Coefficient of Resistance

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ABSTRACT

We successfully grown $\text{La}_{0.75}\text{Sr}_{0.25}\text{MnO}_3/\text{La}_{0.75}\text{Ca}_{0.25}\text{MnO}_3$ multilayers thin films on $\text{SrTiO}_3(001)$ substrates using RF magnetron sputtering. We used the photolithography and ion etching techniques to fabricate the thin film to a 20- μm wide microbridge for standard four-terminal measurement with a gold film evaporated onto electrical leads. In this article, we study the temperature coefficient of resistance (TCR), and the metal-insulator transition temperature (T_p) in LSMO/LCMO multilayers. In the LSMO/LCMO multilayers, we can find that the TCR and T_p are larger than those in the mixed thin films. We also study the effects of oxygen annealing on maximum value of TCR (TCR_{MAX}) and T_p . For the LSMO/LCMO (50 Å / 100 Å)₈ multilayer with oxygen annealing at 800 °C, the value of the T_p is increased from 271.6 K to 282.5 K, and TCR_{MAX} is increased from 7.5 %K⁻¹ to 11.1 %K⁻¹. Here the numbers in parentheses correspond, respectively, to the thicknesses of LSMO and LCMO layers in unit of angstrom, and the subscript denotes the total repeated number of bilayers. Finally, the relationship between TCR_{MAX} and bipolaron binding energy (E_b) is deduced by the current-carrier-density-collapse model. It is found that the TCR_{MAX} increases as E_b is decreased.

Keywords : multilayers ; RF sputter ; temperature coefficient of resistance ; metal-insulator transition temperature ; current-carrier-density-collapse ; bipolaron

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